

20V N-Channel Enhancement Mode MOSFET

Description

The PECN2020SR uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It can be used in a wide variety of applications.

General Features

- ◆ $V_{DS} = 20V$ $I_D = 20A$
 $R_{DS(ON)}(Typ.) = 4.7m\Omega$ @ $V_{GS} = 4.5V$
 $R_{DS(ON)}(Typ.) = 5.1m\Omega$ @ $V_{GS} = 2.5V$
 $R_{DS(ON)}(Typ.) = 6.8m\Omega$ @ $V_{GS} = 1.8V$
- ◆ High density cell design for ultra low $R_{DS(on)}$
- ◆ Fully characterized avalanche voltage and current
- ◆ Good stability and uniformity with high E_{AS}
- ◆ Excellent package for good heat dissipation
- ◆ Special process technology for high ESD capability
- ◆ 100% UIS tested

Application

- ◆ Automotive applications
- ◆ Hard switched and high frequency circuits
- ◆ Uninterruptible power supply

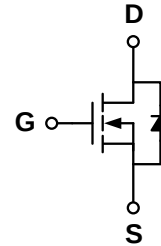
Package

- ◆ SOP-8

100% UIS TESTED!

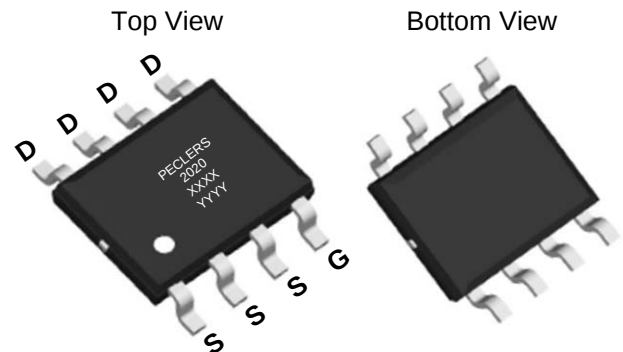
100% ΔV_{ds} TESTED!

Schematic diagram



Marking and pin assignment

SOP-8



PECLERS 2020—Product Name

XXXX—Wafer Lot No.

YYYY—Date Code



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
PECN2020SR	-55°C to +150°C	SOP-8	4000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter		symbol	limit	unit
Drain-source voltage		V_{DS}	20	V
Gate-source voltage		V_{GS}	±12	V
Continuous Drain Current	TC=25°C	I_D	20	A
	TC=70°C		16	
Pulsed Drain Current		I_{DP}	140	A
Avalanche energy(L=0.5mH) ^(note1)		E_{AS}	160	mJ
Maximum power dissipation	TC=25°C	P_D	3.1	W
	TC=70°C		2	

Operating junction Temperature range	Tj	-55—150	°C
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Thermal Characteristics

Parameter		Symbol	Typ	Max	Unit
Maximum Junction-to-Ambient ^A	≤ 10s	R _{θJA}	33	40	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		59	75	
Maximum Junction-to-Lead ^B	Steady-State	R _{θJC}	16	24	

A: The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJC} and lead to ambient.

C: Eas test: VDD=10V, RG=25ohm, L=500Uh

D: Pulse test; pulse width ≤ 300ns, duty cycle ≤ 2%.

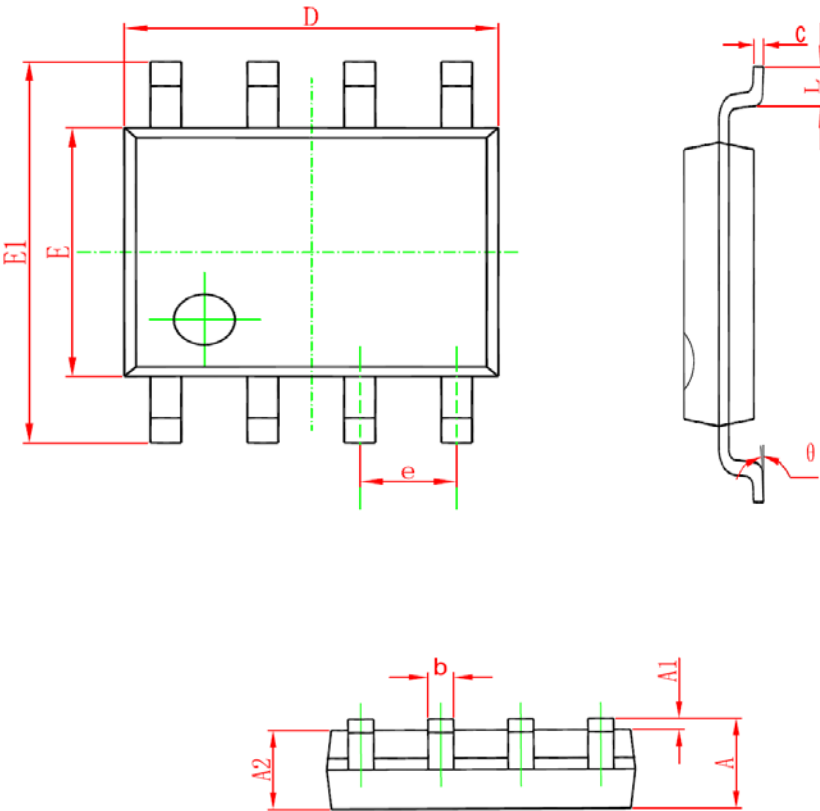
E: Guaranteed by design, not subject to production testing.

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Typ	Max	Unit
Static Characteristics							
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA		20	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	T _J =25°C	-	-	1	μA
			T _J =85°C	-	-	5	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V		-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA		0.5	0.75	1.2	V
Drain-source on-state resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A		-	4.7	5.5	mΩ
		V _{GS} =2.5V, I _D =10A		-	5.1	7	
		V _{GS} =1.8V, I _D =10A			6.8	9	
On Status Drain Current	I _{D(ON)}	V _{DS} =20V, V _{GS} =4.5V		40	-	-	A
Diode Characteristics							
Diode Continuous Forward Current	I _S			-	-	12	A
Reverse Recovery Time	t _{rr}	I _F =10A, dI/dt=20A/us		-	25	-	ns
Reverse Recovery Charge	Q _{rr}			-	24	-	nC
Dynamic Characteristics ²							
Input capacitance	C _{ISS}	V _{GS} =0V ,V _{DS} =10V f=1.0MHz		-	2000	-	pF
Output capacitance	C _{OSS}			-	500	-	
Reverse transfer capacitance	C _{RSS}			-	200	-	
Turn-on delay time	t _{D(ON)}	V _{GS} =4.5V, V _{DD} =10V, I _D =2A		-	6.5	-	ns
Turn-on Rise time	t _r			-	17	-	
Turn-off delay time	t _{D(OFF)}			-	29.5	-	
Turn-off Fall time	t _f			-	17	-	
Total gate charge	Q _g	V _{GS} =4.5V,I _D =10A V _{DS} =10V		-	27		nC
Gate-source charge	Q _{gs}				6.5		
Gate-drain charge	Q _{gd}			-	6.4	-	
Drain-Source Diode Characteristics							
Diode forward voltage	V _{SD}	I _{SD} =10A,V _{GS} =0V		-	0.8	1.2	V

Package Information

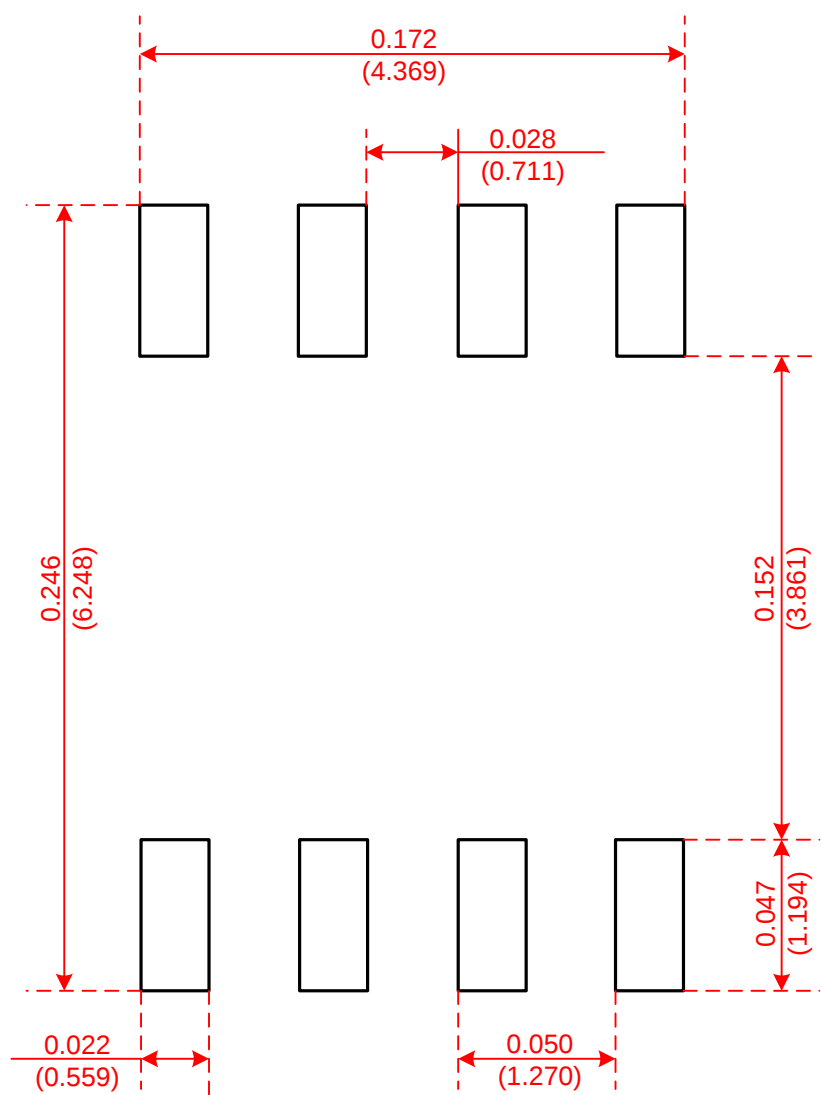
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Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Recommended Minimum Pads

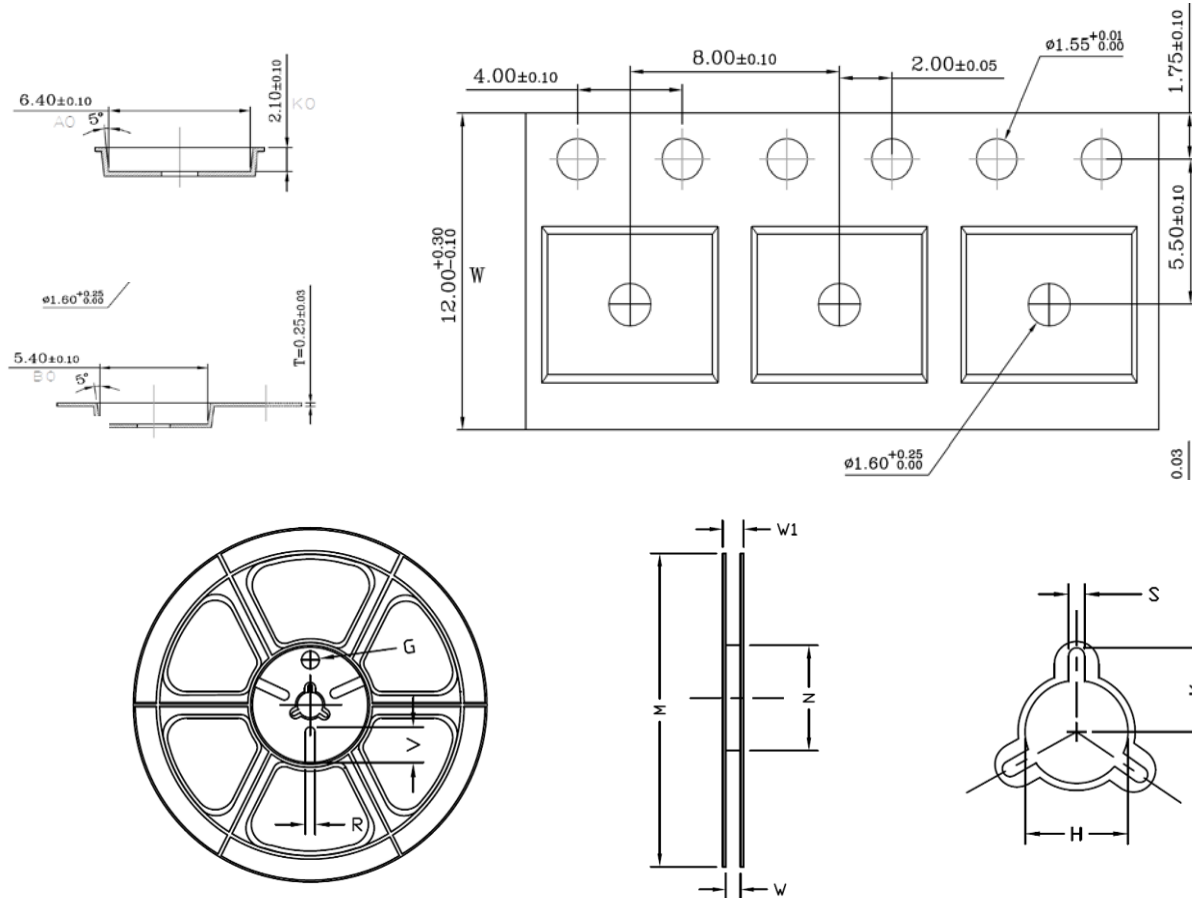
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Recommended Minimum Pads
Dimensions in Inches/(mm)

Tape and Reel

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Tape Size	Reel Size	M	N	W	W1	H	K	S	G	R	V
12mm	Φ330	Φ330.00 ±0.50	Φ97.00 ±0.30	13.00 ±0.30	17.40 ±1.00	Φ13.00 ±0.5	10.6	2.00 ±0.50	—	—	—

Unit Per Reel:
4000pcs

